

VERTICAL DEFLECTION BOOSTER

FEATURES SUMMARY

- POWER AMPLIFIER
- FLYBACK GENERATOR
- THERMAL PROTECTION
- OUTPUT CURRENT UP TO 3.0APP
- FLYBACK VOLTAGE UP TO 70V (on Pin 5)
- SUITABLE FOR DC COUPLING APPLICATION

DESCRIPTION

Designed for monitors and high performance TVs, the TDA8177 vertical deflection booster delivers flyback voltages up to 70V.

The TDA8177 operates with supplies up to 35V and provides up to 3APP output current to drive the yoke.

The TDA8177 is offered in HEPTAWATT package.

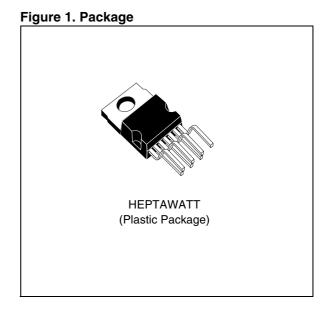
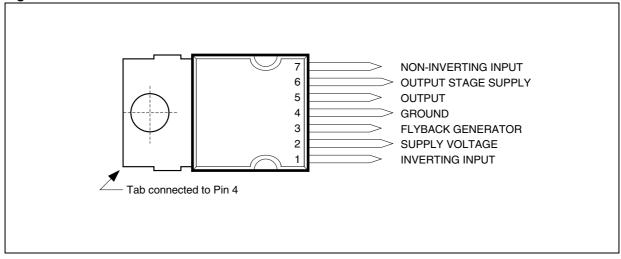


Figure 2. Pin Connections



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Figure 3. Block Diagram

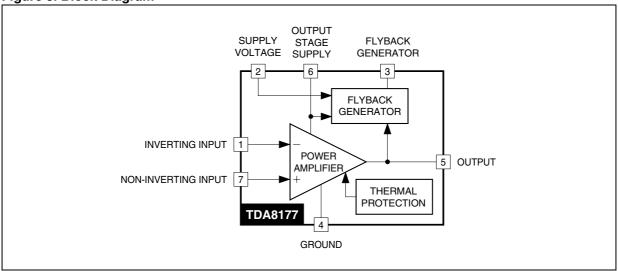


Table 1. Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
Vs	Supply Voltage (Pin 2) (see note 1)	40	V
V ₆	Flyback Peak Voltage (Pin 6) (see note 1)	75	V
V ₁ , V ₇	Amplifier Input Voltage (Pins 1-7) (see note 1)	- 0.3, + V _S	V
lo	Maximum Output Peak Current (see notes 2 and 3)	2.5	Α
l ₃	Maximum Sink Current (first part of flyback) (t < 1ms)	2.5	Α
I ₃	Maximum Source Current (t < 1ms)	2.5	Α
V _{ESD}	Electrostatic Handling for all pins (see note 4)	2000	V
T _{OPER}	Operating Ambient Temperature	- 20, + 75	°C
T _{STG,}	Storage Temperature	- 40, + 150	°C
Tj	Junction Temperature	+ 150	°C

Note: 1. Versus Pin 4.

- The output current can reach 4A peak for t ≤ 10µs (up to 120Hz).
 Provided SOAR is respected (see Figures 6 and 7).
 Equivalent to discharging a 100pF capacitor through a 1.5kΩ series resistor.

Table 2. Thermal Data

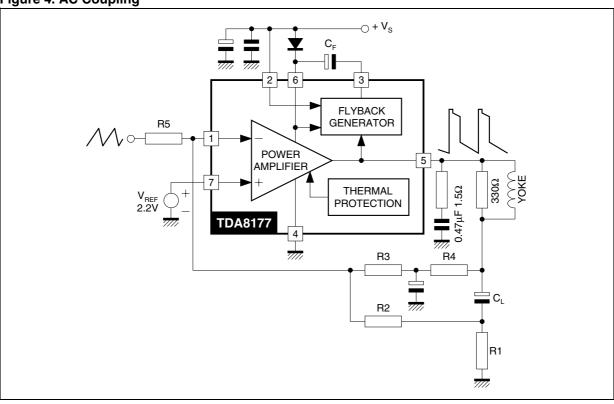
Symbol	Parameter	Value	Unit
R _{th (j-c)}	Junction-case Thermal Resistance Max	3	°C/W
T _t	Temperature for Thermal Shutdown	150	°C
T _{jr}	Recommended Max. Junction Temperature	120	°C

Table 3. ELECTRICAL CHARACTERISTICS ($V_S = 35V$, $T_A = 25^{\circ}C$, unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Vs	Operating Supply Voltage Range		10		35	V
l ₂	Pin 2 Quiescent Current	I ₃ = 0, I ₅ = 0		9	20	mA
I ₆	Pin 6 Quiescent Current	$I_3 = 0$, $I_5 = 0$, $V_6 = 35V$	8	15	30	mA
I _O	Max. Peak Output Current				1.5	Α
I ₁	Amplifier Bias Current	V ₁ = 22V, V ₇ = 23V		-0.15	- 1	μА
I ₇	Amplifier Bias Current	V ₁ = 23V, V ₇ = 22V		-0.15	- 1	μА
V _{IO}	Offset Voltage				7	mV
ΔV _{IO} /dt	Offset Drift versus Temperature			- 10		μV/°C
GV	Voltage Gain		80			dB
V _{5L}	Output Saturation Voltage to GND (Pin 4)	I ₅ = 1.5A		1	1.7	V
V _{5H}	Output Saturation Voltage to Supply (Pin 6)	I ₅ = - 1.5A		1.8	2.3	V
V _{D5 - 6}	Diode Forward Voltage between Pins 5-6	I ₅ = 1.5A		1.8	2.3	V
V _{D3 - 2}	Diode Forward Voltage between Pins 3-2	I ₃ = 1.5A		1.6	2.2	V
V _{3SL}	Saturation Voltage on Pin 3	I ₃ = 20mA		0.4	1	V
V _{3SH}	Saturation Voltage to Pin 2 (2nd part of flyback)	I ₃ = 1.5A		2.1	2.8	V

APPLICATION CIRCUITS

Figure 4. AC Coupling





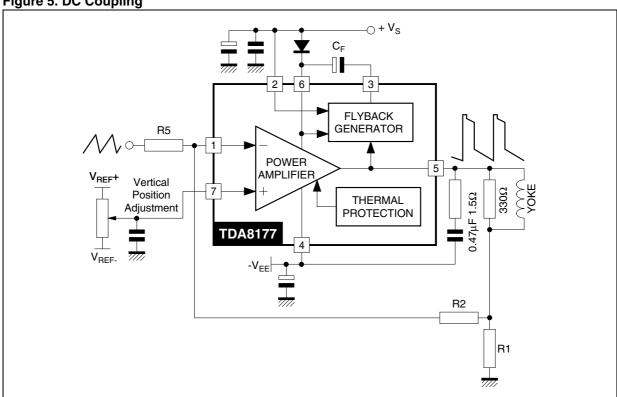


Figure 6. Output Transistors SOA

(for secondary breakdown)

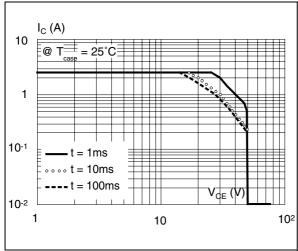
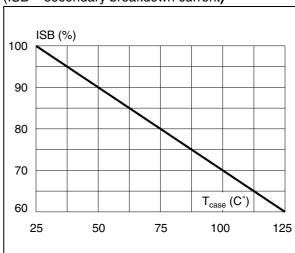


Figure 7. Secondary Breakdown Temperature **Derating Curve**

(ISB = secondary breakdown current)



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PART NUMBERING

Table 4. Order Codes

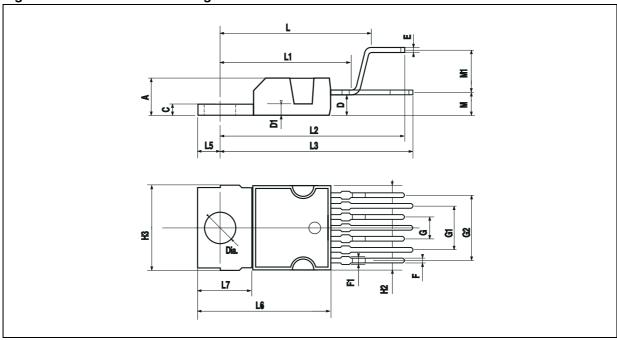
Part Number	Package	Temperature Range		
TDA8177	HEPTAWATT7	-20 to 75 °C		

PACKAGE MECHANICAL

Table 5. HEPTAWATT7 - Mechanical Data

Symbol	millimeters			inches			
	Min	Тур	Max	Min	Тур	Max	
Α			4.8			0.189	
С			1.37			0.054	
D	2.4		2.8	0.094		0.110	
D1	1.2		1.35	0.047		0.053	
Е	0.35		0.55	0.014		0.022	
F	0.6		0.8	0.024		0.031	
F1			0.9			0.035	
G	2.41	2.54	2.67	0.095	0.100	0.105	
G1	4.91	5.08	5.21	0.193	0.200	0.205	
G2	7.49	7.62	7.8	0.295	0.300	0.307	
H2			10.4			0.409	
НЗ	10.05		10.4	0.396		0.409	
L		16.97			0.668		
L1		14.92			0.587		
L2		21.54			0.848		
L3		22.62			0.891		
L5	2.6		3	0.102		0.118	
L6	15.1		15.8	0.594		0.622	
L7	6		6.6	0.236		0.260	
М		2.8			0.110		
M1		5.08			0.200		
Dia.	3.65		3.85	0.144		0.152	

Figure 8. HEPTAWATT7 - Package Dimensions



Note: Drawing is not to scale

REVISION HISTORY

Table 6. Revision History

Date	Revision	Description of Changes
December-1998	1	First Issue
14-May-2004	2	Stylesheet update. No content change.

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